IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent No	7,053,010 B2
Patent Issue Date	May 30, 2006
Application Serial No	10/806,923
Filing Date	March 22, 2004
Assignee Micr	on Technology, Inc.
Inventorship	Weimin Li et al.
Attorney's Docket No	Mi22-2274
Title: Methods of Depositing Silicon Dioxide Compris	ing Layers in the
Fabrication of Integrated Circuitry, Methods of Forming Arrays of Memory Cells	ng Trench Isolation,

REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT FOR APPLICANT MISTAKES and PTO MISTAKES (37 C.F.R. §§ 1.322(a) and 1.323)

To:

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

ATTN:

Decision and Certificate of Correction

Branch of the Patent Issue Division

From:

Mark S. Matkin (Tel. 509-624-4276; Fax 509-838-3424)

Wells St. John P.S.

601 W. First Avenue, Suite 1300

Spokane, WA 99201-3828

Sir:

It is hereby requested that a Certificate of Correction be issued with respect to Patent No. 7,053,010 B2, granted May 30, 2006, in accordance with the Certificate of Correction form attached hereto.

It is noted that errors appear in this patent of a typographical nature of character, as more fully described below. The errors occurred in good faith. Correction thereof does not involve such changes in the patent as would constitute new matter or would require re-examination.

Other errors listed on the Certificate of Correction form were apparently incurred through the fault of the PTO as will be disclosed by the records of files in the Office.

Attached hereto, in duplicate, is Form PTO-1050, with at least one copy being suitable for printing.

The exact page and line number where the errors occur in the application file are:

Page 52, claim 131;

Page 53, claim 139;

Page 56, claim 152;

Page 56, claim 156.

The Commissioner is hereby authorized to charge payment of any applicable fees to Deposit Account No. 23-0925, as required by 37 CFR 1.20(a).

Respectfully submitted,

Dated: 3 -26-07

Mark S. Matkin Reg. No. 32,268

UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO. : 7,053,010 B2

DATED

: May 30, 2006

INVENTOR(S) : Li et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 4. line 6, please delete "H₃" before "species" and insert --CH₃--.

Col. 6, line 6, please delete "bond-is" after "silicon-nitrogen" and insert -bond is--.

Col. 18, line 1, claim 131, please delete "herein" after "claim 129" and insert --wherein--.

Col. 18, line 26, claim 139, please delete "herein" after "claim 127" and insert --wherein--.

Col. 19, line 14, claim 152, please delete "herein" after "claim 150" and insert --wherein--.

Col. 19, line 21, claim 156, please delete "herein" after "claim 148" and insert --wherein--.

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Mailing Address of Sender:

Mark S. Matkin Wells St. John P.S. 601 West First Avenue, Suite 1300 Spokane, WA 99201-3828

Patent No. 7,053,010 B2